TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2 S C 5 2 4 2

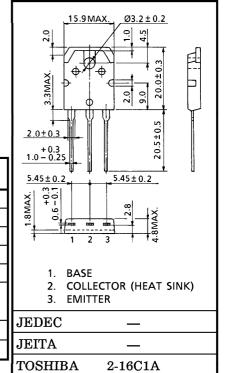
POWER AMPLIFIER APPLICATIONS

- High Collector Breakdown Voltage: VCEO=230V (Min.)
- Complementary to 2SA1962
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	230	V
Collector-Emitter Voltage	VCEO	230	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	15	A
Base Current	$I_{\mathbf{B}}$	1.5	A
Collector Power Dissipation (Tc=25°C)	PC	130	w
Junction Temperature	Tj	150	°C
Storage Temperature	$\mathrm{T_{stg}}$	-55~150	°C

Unit in mm



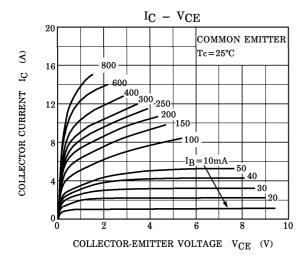
Weight: 4.7g (Typ.)

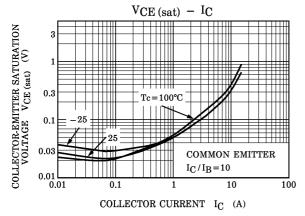
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

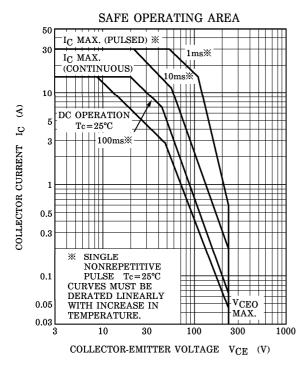
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 230V, I_{E} = 0$	_	_	5.0	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=5V, I_{C}=0$	_	_	5.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C} = 50 {\rm mA}, \ I_{\rm B} = 0$	230	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{\rm CE}$ =5V, I _C =1A	55	_	160	
	h _{FE (2)}	$V_{CE}=5V, I_{C}=7A$	35	60	_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{\rm C}$ =8A, $I_{\rm B}$ =0.8A	_	0.4	3.0	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE}=5V, I_{C}=7A$	_	1.0	1.5	V
Transition Frequency	$ m f_{T}$	$V_{CE}=5V, I_{C}=1A$	_	30	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	200	_	pF

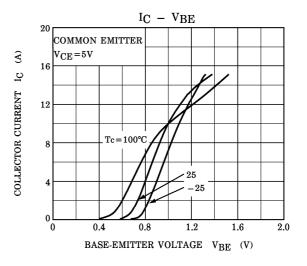
(Note): $h_{FE(1)}$ Classification R: 55~110, O: 80~160

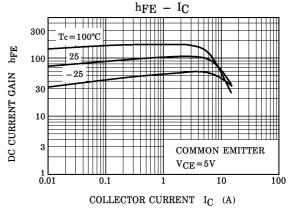
1 2001-11-05











2 2001-11-05

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